Average gate power dissipation (T_j=150)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =150 R_L =3.3kΩ	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	40	mA
				50	
I_H	I_T =100mA		MAX.	30	mA
dV/dt	V_D=400V Gate Open T_j =150		MIN.	1200	V/μs
(dI/dt)c	(dV/dt)c =20V/μs, T_j=150		MIN.	8	A/ms
t_{on}	I_G=40mA I_A=200mA I_R=20mA T_j=25		TYP.	3	μs
t_{off}				30	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM} =5.5A t_p=380μs	T_j=25	1 .4	V
V_{TO}	Threshold voltage	T_j=150	0 .6	V
R_D	Dynamic resistance	T_j=150	129	mΩ
I_{DRM}	V_D =V_{DRM} V_R =V_{RRM}	T_j=25	5	μA
I_{RRM}		T_j=150	0 .8	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	4	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W

ORDERING INFORMATION

T	04	35	H	-6	F

- T: Triacs
- 04: $I_{T(RMS)}$:4A
- 35: I_{GT1-3} 035mA
- H: High junction temperature
- -6: V_{DRM} /V_{RRM} 1600V
- F: F:TO-220F(Ins)

MARKING

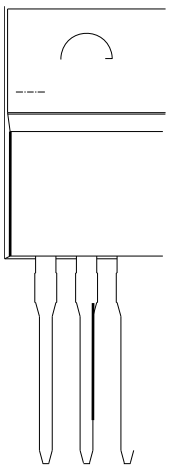

FIG.1: Maximum power dissipation versus RMS on-state current

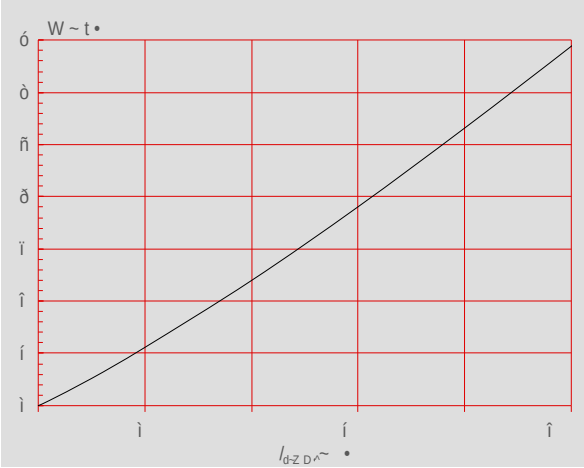

FIG.2: RMS on-state current versus case temperature

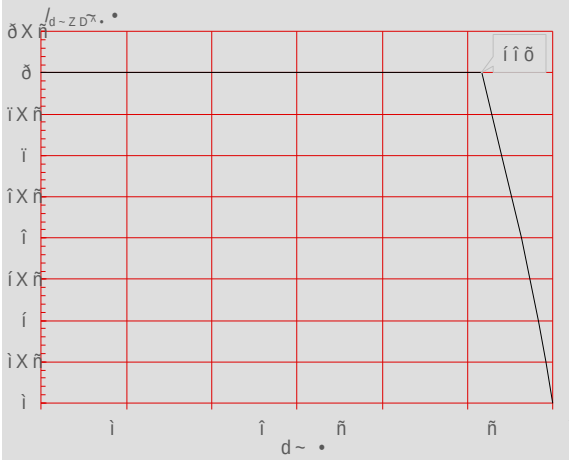

FIG.3: Surge peak on-state current versus number of cycles

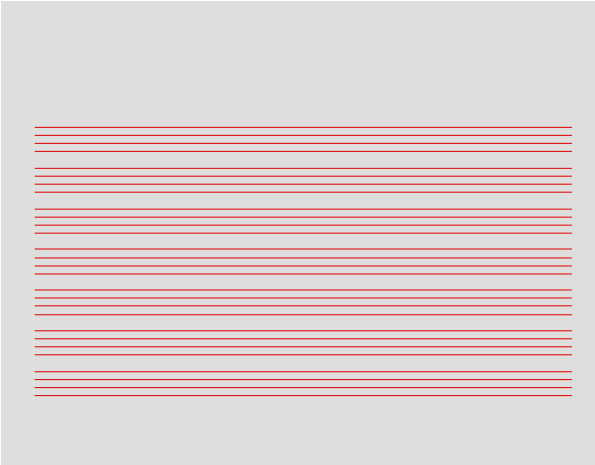

FIG.4: On-state characteristics

ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(Ma)	Package	Base qty. (pcs)	Delivery mode
		- -			
T0435H-6F	600	35	TO-220F(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.10, 2023	A.1.0	Last updated
Oct.10, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

PACKAGE MECHANICAL DATA

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